

## N-Channel Enhancement Mode Power MOSFET

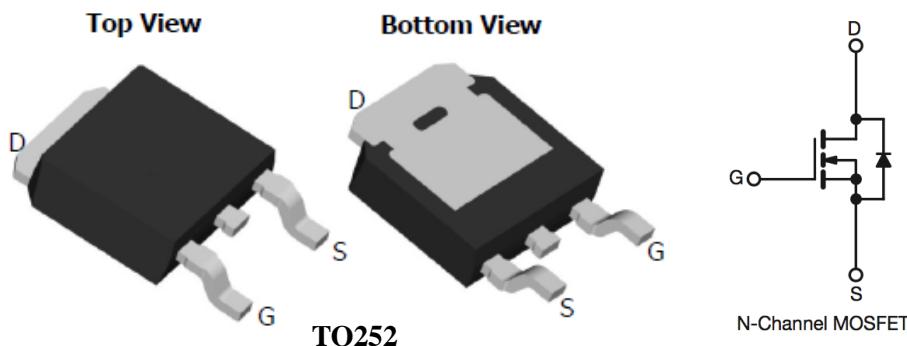
### ● Features

$V_{DS}$	$R_{DS(ON)TYP}$	$I_D$
20V	9.5 mΩ@4.5V	50.7A
	13.5mΩ@2.5V	

### ● General Description

- Synchronous Rectification in DC/DC and AC/DC Converters
- Industrial and Motor Drive applications

### ● Pin Configurations



### ● Absolute Maximum Ratings @ $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter		Symbol	Ratings	Unit
Drain-Source Voltage		$V_{DSS}$	20	V
Gate-Source Voltage		$V_{GSS}$	$\pm 12$	V
Drain Current (Continuous) *AC	$T_c=25^\circ\text{C}$	$I_D$	50.7	A
	$T_c=70^\circ\text{C}$		40.6	
Drain Current (Pulse) *B		$I_{DM}$	200	A
Power Dissipation	$T_c=25^\circ\text{C}$	$P_D$	46	W
Operating Temperature/ Storage Temperature		$T_J/T_{STG}$	-55~150	°C

### ● Thermal Resistance Ratings

Parameter		Symbol	Maximum	Unit
Maximum Junction-to-Ambient	Steady State	$R_{thJA}$	2.7	°C/W
Maximum Junction-to-Case (Drain)	Steady State	$R_{thJC}$	50	

## Electrical Characteristics

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$T_A=25^\circ\text{C}$  unless otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(\text{BR})\text{DSS}}$	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	20	--	--	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$	--	--	1	$\mu\text{A}$
Gate Threshold Voltage	$V_{GS(\text{TH})}$	$V_{GS} = V_{DS}, I_{DS} = 250\mu\text{A}$	0.4	0.65	1.2	V
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12\text{V}, V_{DS} = 0\text{V}$	--	--	$\pm 100$	nA
Drain-Source On-state Resistance	$R_{DS(\text{on})}$	$V_{GS} = 4.5\text{V}, I_D = 6\text{A}$	--	9.5	12	$\text{m}\Omega$
	$R_{DS(\text{on})}$	$V_{GS} = 2.5\text{V}, I_D = 5\text{A}$	--	13.5	18	$\text{m}\Omega$
Diode Forward Voltage	$V_{SD}$	$I_{SD} = 1\text{A}, V_{GS} = 0\text{V}$	--	0.73	1.2	V
Diode Forward Current *AC	$I_S$	$T_C = 25^\circ\text{C}$	--	--	50.7	A
<b>Switching</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 15\text{V}, I_D = 20\text{A}, V_{GS} = 5\text{V}$	--	10	--	nC
Gate-Source Charge	$Q_{gs}$		--	3.6	--	nC
Gate-Drain Charge	$Q_{gd}$		--	2.9	--	nC
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{V}, I_D = 1\text{A}, V_{GS} = 10\text{V}, R_{GEN} = 6\Omega$	--	12	--	ns
Turn-on Rise Time	$t_r$		--	4	--	ns
Turn-off Delay Time	$t_{d(off)}$		--	32	--	ns
Turn-Off Fall Time	$t_f$		--	6	--	ns
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	--	1180	--	pF
Output Capacitance	$C_{oss}$		--	270	--	pF
Reverse Transfer Capacitance	$C_{rss}$		--	145	--	pF

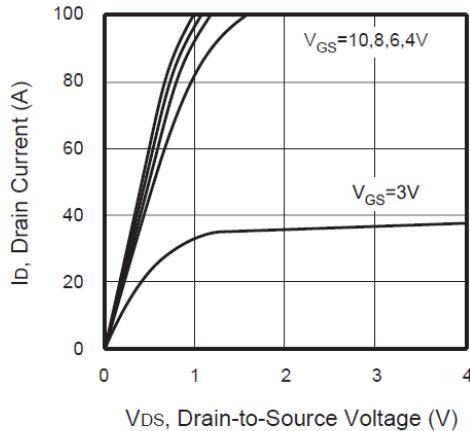
A: The value of  $R_{\theta JA}$  is measured with the device mounted on 1in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with  $T_A=25^\circ\text{C}$ . The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

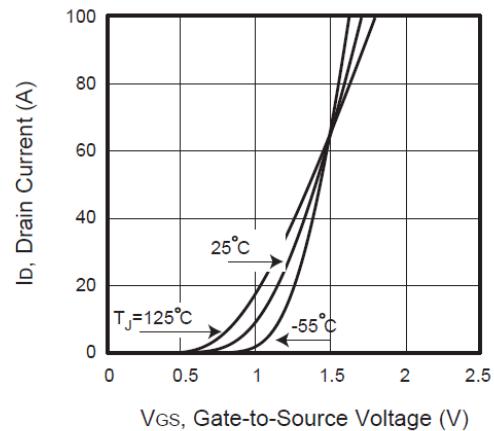
C: The current rating is based on the  $t \leq 10\text{s}$  junction to ambient thermal resistance rating.

# Typical Electrical and Thermal Characteristics

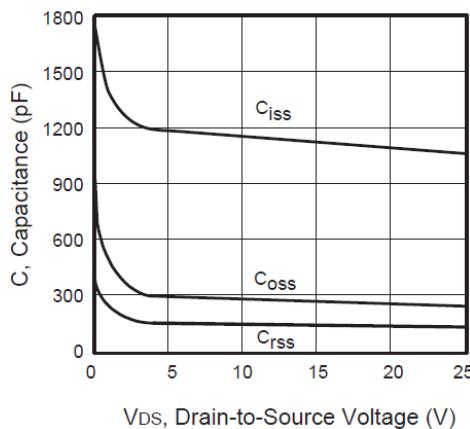
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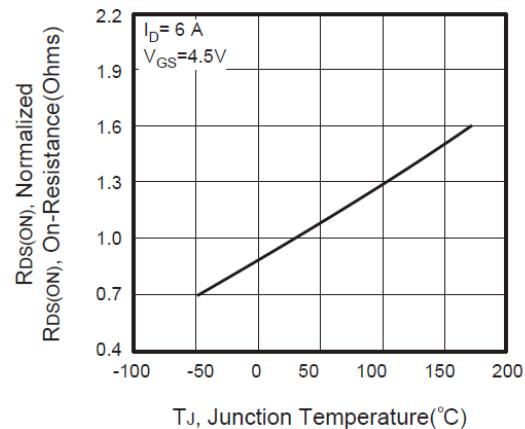
**Figure 1. Output Characteristics**



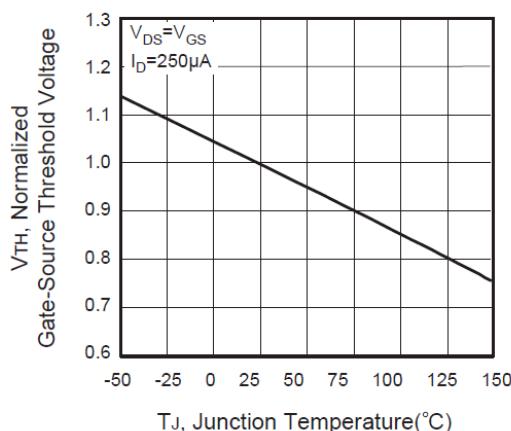
**Figure 2. Transfer Characteristics**



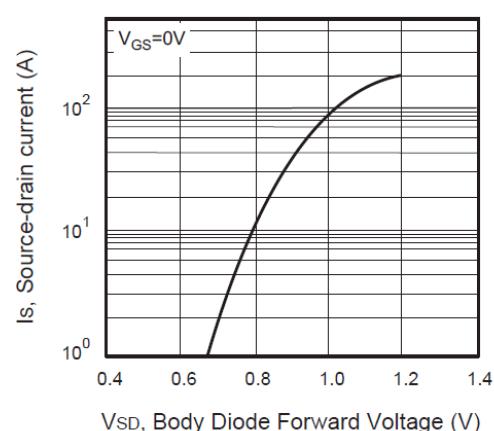
**Figure 3. Capacitance**



**Figure 4. On-Resistance Variation with Temperature**



**Figure 5. Gate Threshold Variation with Temperature**



**Figure 6. Body Diode Forward Voltage Variation with Source Current**

## Typical Electrical and Thermal Characteristics

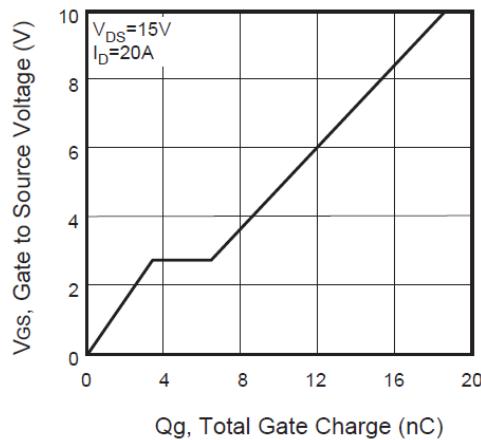


Figure 7. Gate Charge

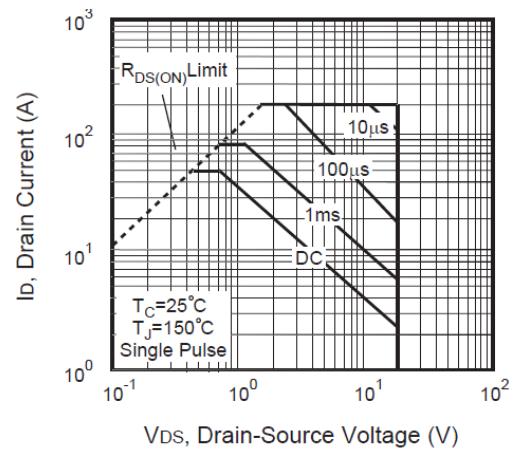


Figure 8. Maximum Safe Operating Area

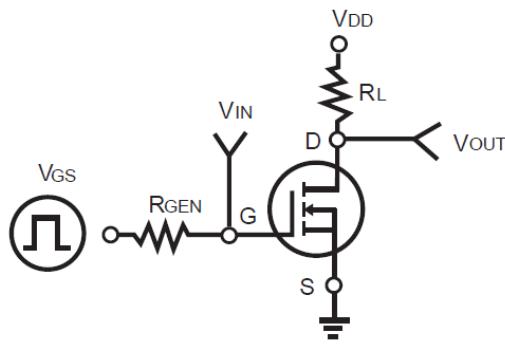


Figure 9. Switching Test Circuit

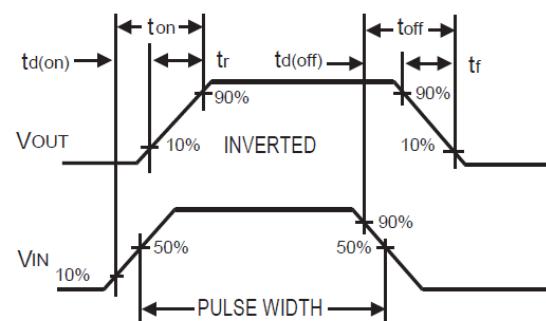


Figure 10. Switching Waveforms

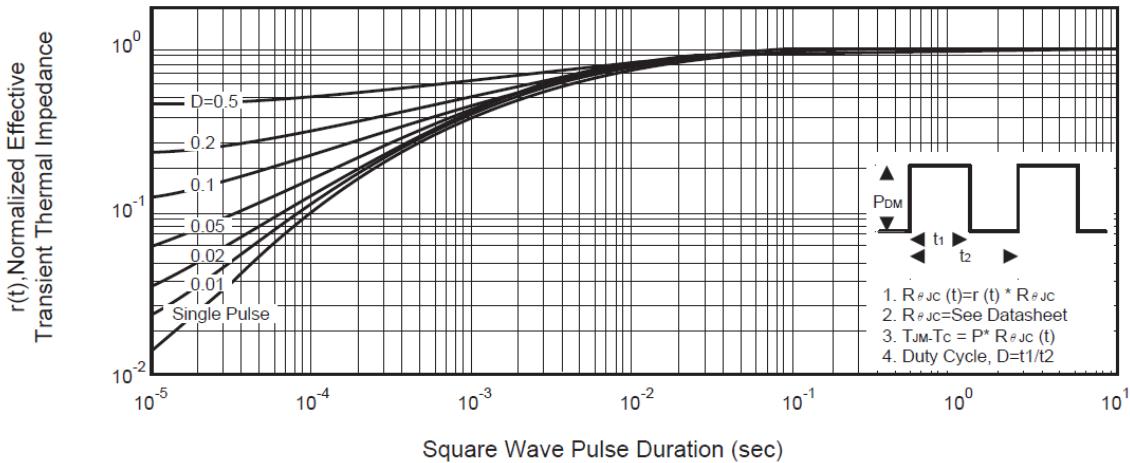
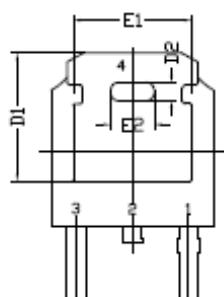
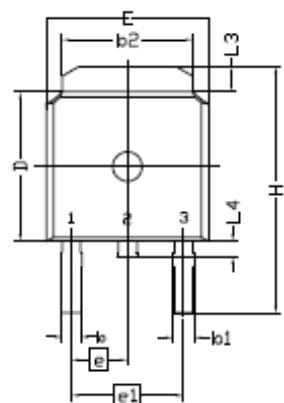
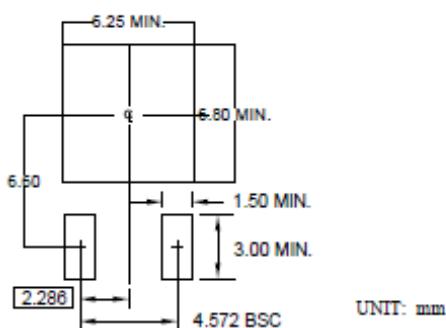


Figure 11. Normalized Thermal Transient Impedance Curve

## Package Information



RECOMMENDED LAND PATTERN



NOTE

1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS. MOLD FLASH SHOULD BE LESS THAN 6 MILS.
2. DIMENSION L IS MEASURED IN GAUGE PLANE
3. TOLERANCE 0.10 mm UNLESS OTHERWISE SPECIFIED
4. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.
5. REFER TO JEDEC TO-252 (AA)

SYMBOL	DIMENSION IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	2.184	2.286	2.388	0.086	0.090	0.094
A1	0.000	---	0.127	0.000	---	0.005
A2	0.889	1.041	1.143	0.035	0.041	0.045
b	0.635	0.762	0.889	0.025	0.030	0.035
b1	0.762	0.840	1.143	0.030	0.033	0.045
b2	4.953	5.340	5.461	0.195	0.210	0.215
c	0.450	0.508	0.610	0.018	0.020	0.024
c1	0.450	0.508	0.610	0.018	0.020	0.024
D	5.969	6.096	6.223	0.235	0.240	0.245
D1	5.210	5.249	5.380	0.205	0.207	0.212
D2	0.662	0.762	0.862	0.026	0.030	0.034
E	6.350	6.604	6.731	0.250	0.260	0.265
E1	4.318	4.826	4.901	0.170	0.190	0.193
E2	1.678	1.778	1.878	0.066	0.070	0.074
e	2.286 BSC			0.090 BSC		
e1	4.572 BSC			0.180 BSC		
H	9.398	10.033	10.414	0.370	0.395	0.410
L	1.270	1.520	2.032	0.050	0.060	0.080
L1	2.921 REF.			0.115REF.		
L2	0.408	0.508	0.608	0.016	0.020	0.024
L3	0.889	1.016	1.270	0.035	0.040	0.050
L4	0.635	---	1.016	0.025	---	0.040